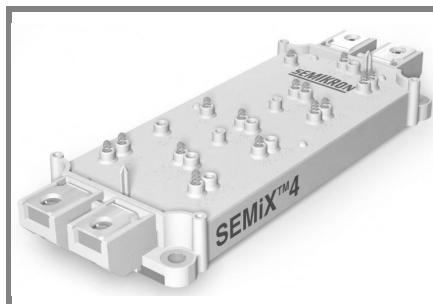


SEMiX754GB128Ds



SEMiX® 4s

SPT IGBT Modules

SEMiX754GB128Ds

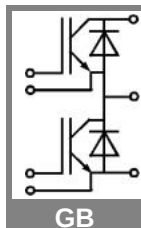
Target Data

Features

- Homogeneous Si
- SPT = Soft-Punch-Through technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

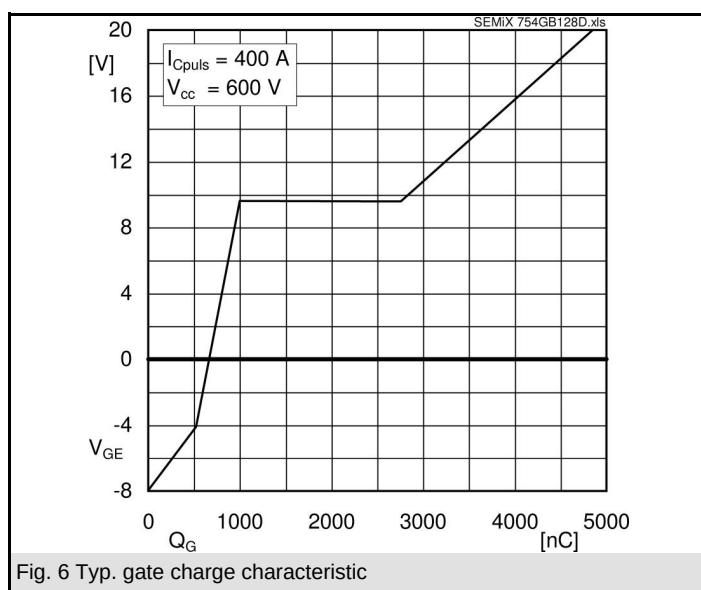
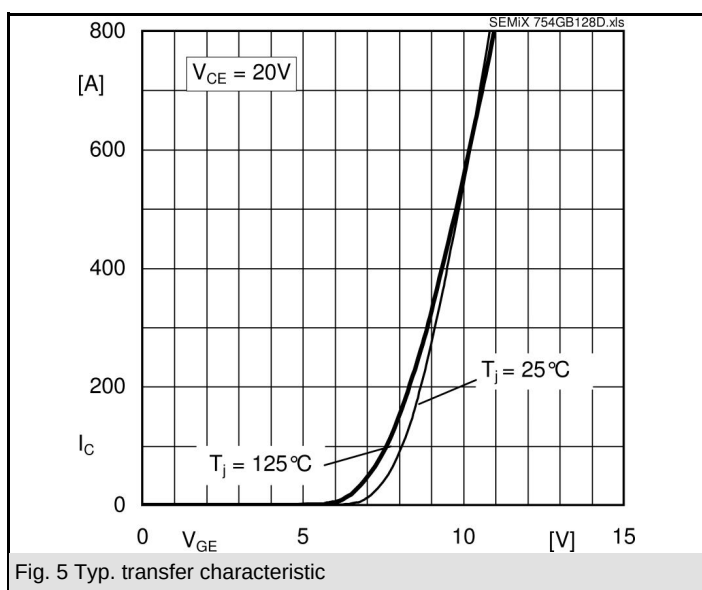
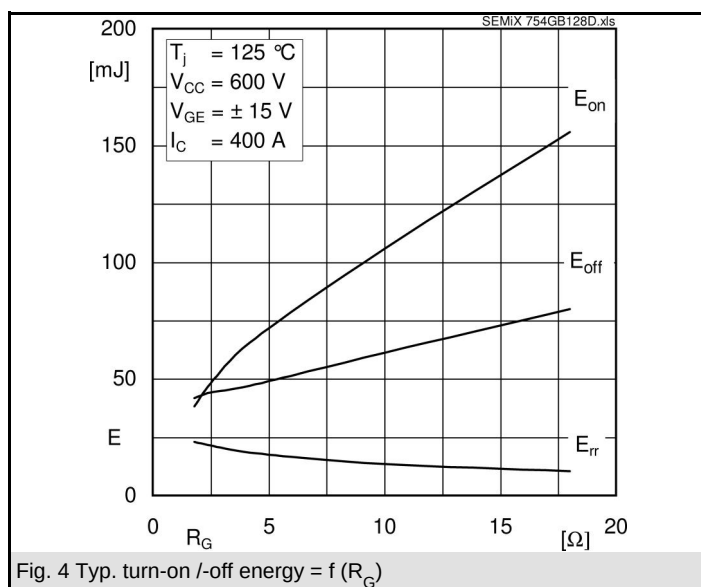
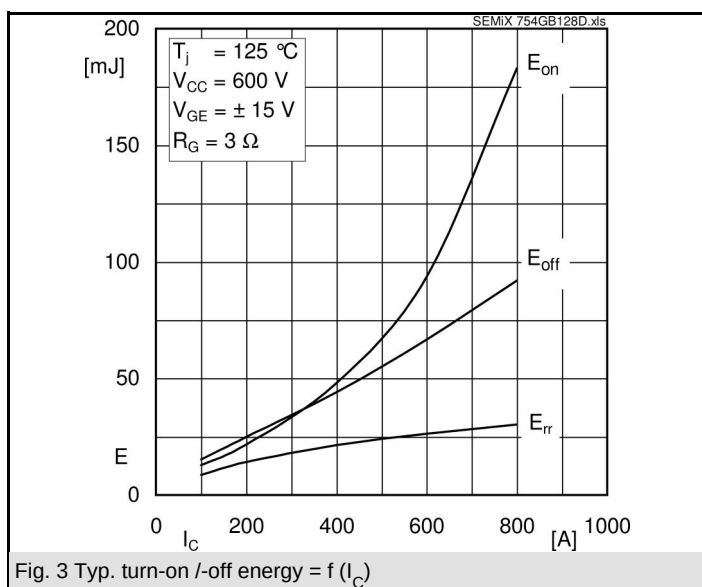
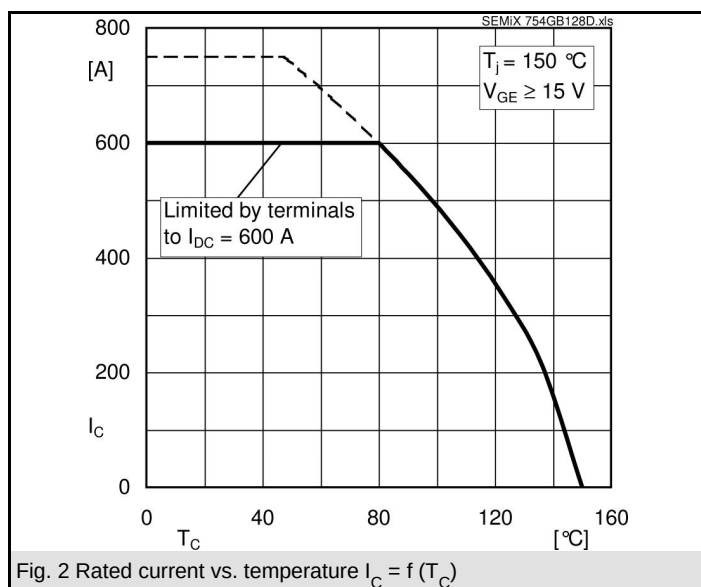
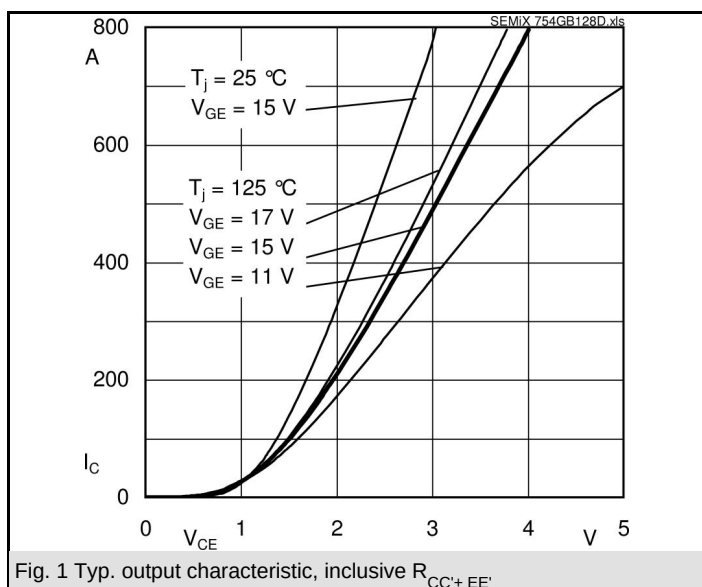
Typical Applications

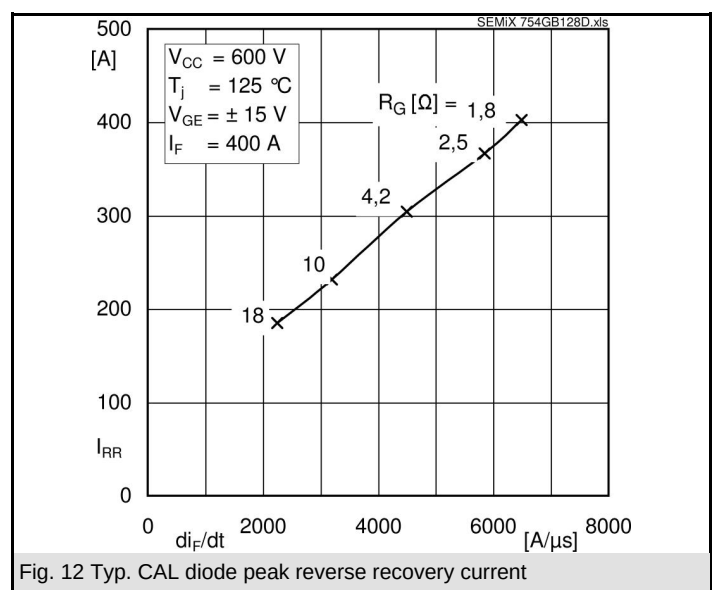
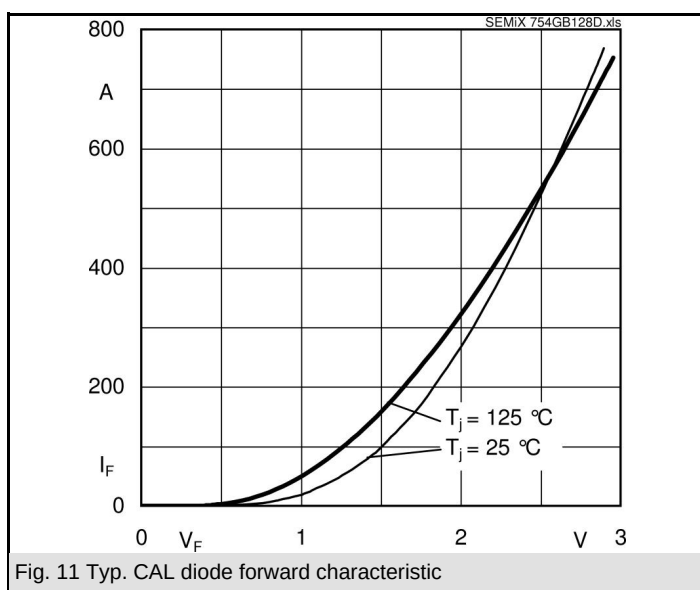
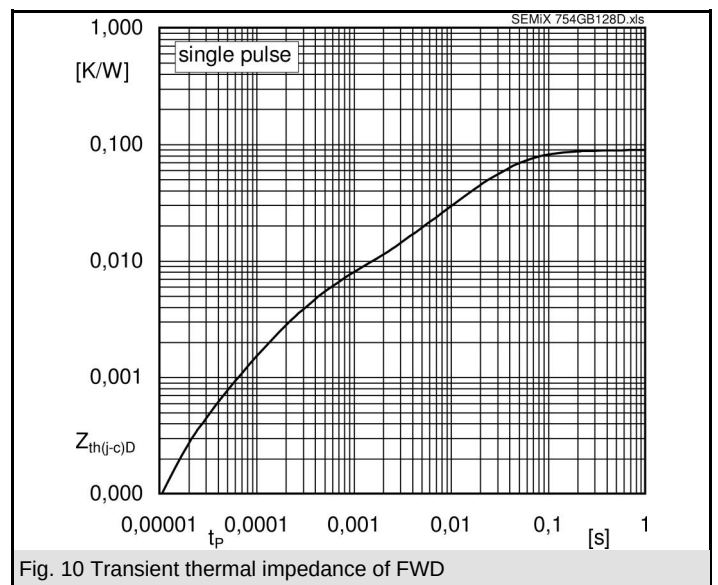
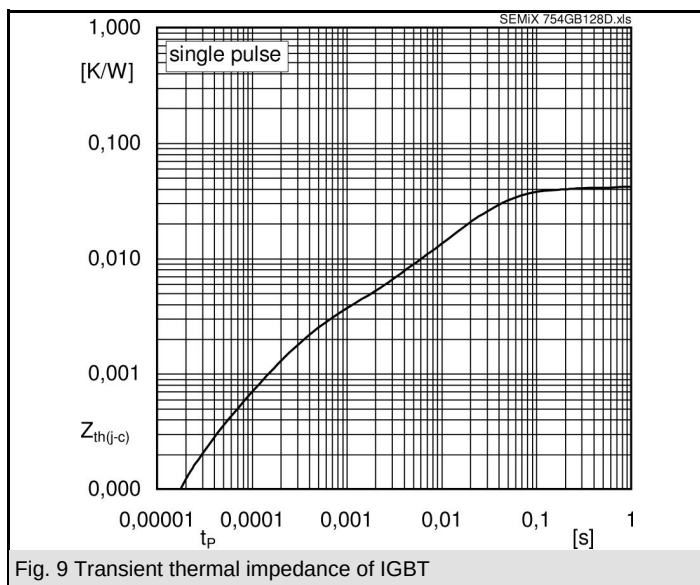
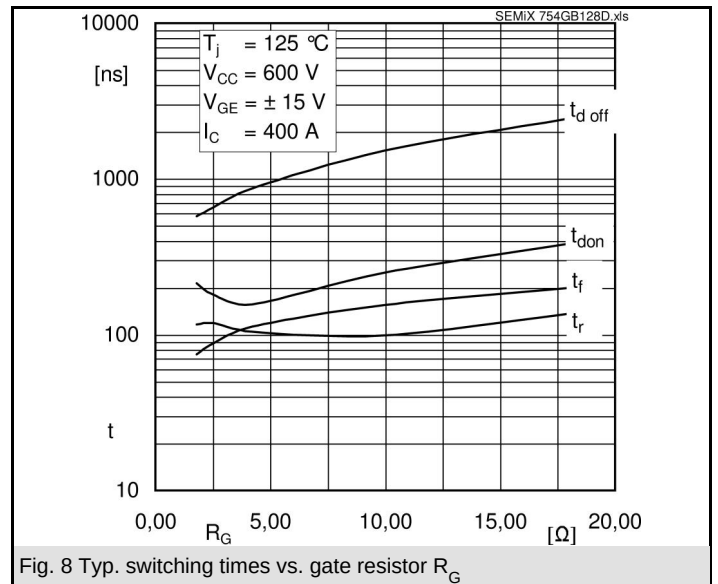
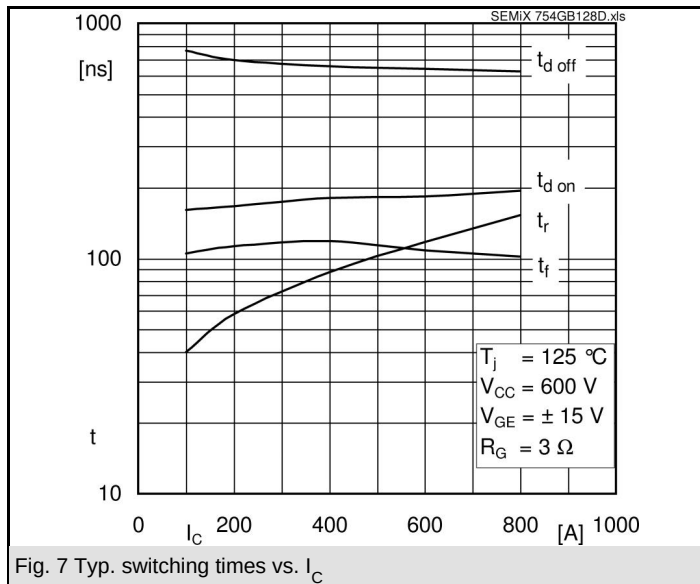
- AC inverter drives
- UPS
- Electronic welders up to 20 kHz

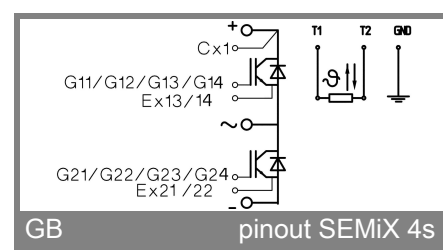
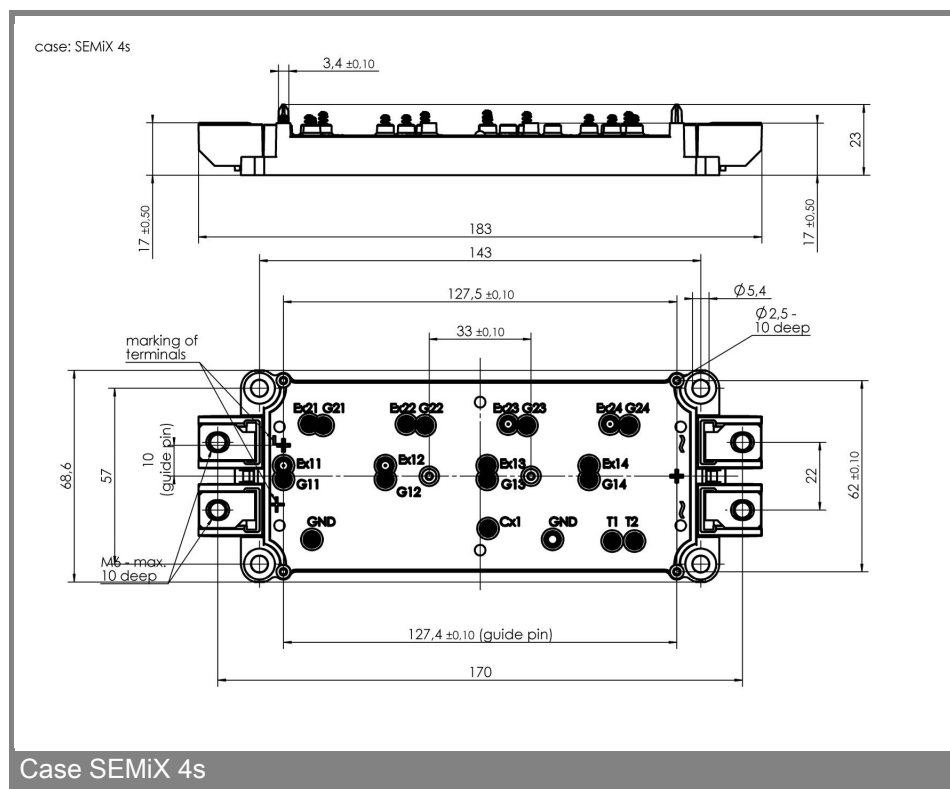
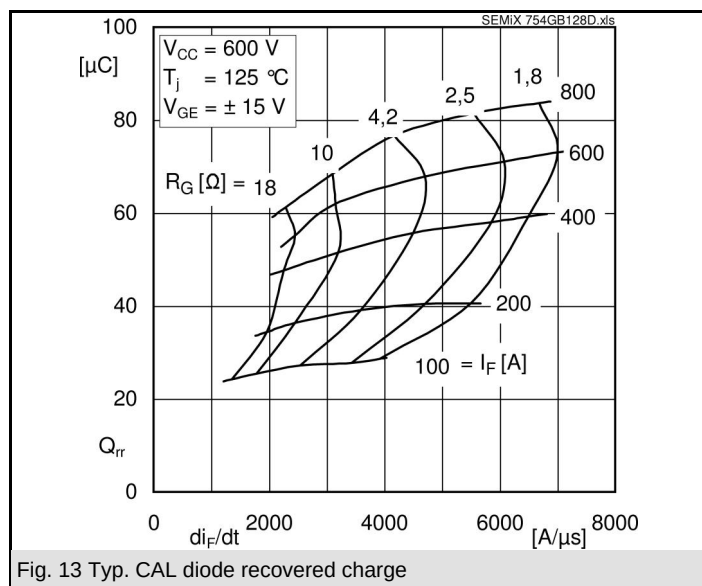


Absolute Maximum Ratings		$T_{case} = 25^{\circ}C$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25 (80)^{\circ}C$	750 (530)	A
I_{CRM}	$t_p = 1 \text{ ms}$	800	A
V_{GES}		± 15	V
T_{vj} , (T_{stg})	$T_{OPERATION} \leq T_{stg}$	-40 ... + 150 (125)	$^{\circ}C$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^{\circ}C$	530 (360)	A
I_{FRM}	$t_p = 1 \text{ ms}$	800	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 25^{\circ}C$	3100	A

Characteristics		$T_{case} = 25^{\circ}C$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 16 \text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25 (^{\circ})^{\circ}C$		0,2	0,6	mA
$V_{CE(TO)}$	$T_j = 25 (125)^{\circ}C$		1 (0,9)	1,15 (1,05)	V
r_{CE}	$V_{GE} = 15 \text{ V}$, $T_j = 25 (125)^{\circ}C$		2,3 (3)	2,9 (3,8)	m Ω
$V_{CE(sat)}$	$I_{Cnom} = 400 \text{ A}$, $V_{GE} = 15 \text{ V}$, $T_j = 25 (125)^{\circ}C$, chip level	1,7	1,9 (2,1)	2,35 (2,55)	V
C_{ies}	under following conditions		36		nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25 \text{ V}$, $f = 1 \text{ MHz}$		2,7		nF
C_{res}			1,7		nF
L_{CE}			22		nH
$R_{CC'+EE'}$	terminal-chip, $T_c = 25 (125)^{\circ}C$		0,7 (1)		m Ω
$t_{d(on)}/t_r$	$V_{CC} = 600 \text{ V}$, $I_{Cnom} = 400 \text{ A}$		180 / 88		ns
$t_{d(off)}/t_f$	$V_{GE} = \pm 15 \text{ V}$		655 / 1118		ns
$E_{on} (E_{off})$	$R_{Gon} = R_{Goff} = 2,5 \Omega$, $T_j = 125^{\circ}C$		44 (48)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 400 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_j = 25 (125)^{\circ}C$, chip level		2 (1,8)	2,5 (2,3)	V
$V_{(TO)}$	$T_j = 25 (125)^{\circ}C$		1,1	1,5 (1,3)	V
r_T	$T_j = 25 (125)^{\circ}C$		2,3	2,5 (2,5)	m Ω
I_{RRM}	$I_{Fnom} = 400 \text{ A}$; $T_j = 25 (125)^{\circ}C$		367		A
Q_{rr}	$di/dt = 5850 \text{ A}/\mu\text{s}$		58		μC
E_{rr}	$V_{GE} = -15 \text{ V}$		21,5		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,042	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,09	K/W
$R_{th(j-c)FD}$	per FWD				K/W
$R_{th(c-s)}$	per module		0,03		K/W
Temperature sensor					
R_{25}	$T_c = 25^{\circ}C$		5 $\pm$ 5%		k Ω
$B_{25/85}$	$R_2 = R_1 \exp[B(1/T_2 - 1/T_1)]$; $T[K]$; B		3420		K
Mechanical data					
M_s/M_t	to heatsink (M5) / for terminals (M6)	3/2,5		5 / 5	Nm
w			390		g







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.